

SANYO Semiconductors DATA SHEET

N-Channel Silicon MOSFET

2SK3352—General-Purpose Switching Device **Applications**

Features

- · Low ON-resistance.
- · Ultrahigh-speed switching.
- 4V drive.
- DC / DC converter applications.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		30	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ΙD		45	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	80	Α
Allowable Power Dissipation	Do		1.65	W
	PD	Tc=25°C	40	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Linit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	30			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =30V, V _{GS} =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	VGS(off)	VDS=10V, ID=1mA	1.0		2.4	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =20A	19	27		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =20A, V _{GS} =10V		11	15	mΩ
	RDS(on)2	ID=10A, VGS=4.5V		15	21	mΩ
Input Capacitance	Ciss	V _{DS} =10V, f=1MHz		1400		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		420		pF
Reverse Transfer Capacitance	Crss	V _{DS} =10V, f=1MHz		210		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		14		ns
Rise Time	t _r	See specified Test Circuit.		530		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		100		ns
Fall Time	tf	See specified Test Circuit.		150		ns

Marking: K3352 Continued on next page.

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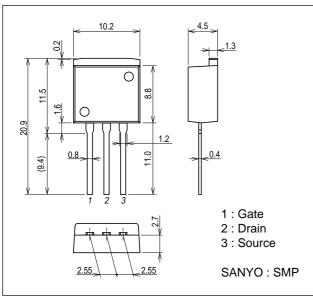
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Onn
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =10V, I _D =20A		28		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =10V, I _D =20A		4.6		nC
Gate-to-Drain Charge	Qgd	V _{DS} =10V, V _{GS} =10V, I _D =20A		5		nC
Diode Forward Voltage	VSD	IS=45A, VGS=0V		1.0	1.2	V

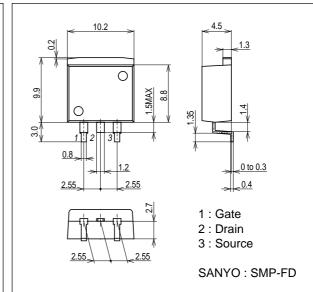
Package Dimensions

unit : mm 7513-002



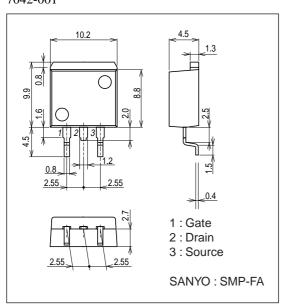
Package Dimensions

unit : mm 7001-003

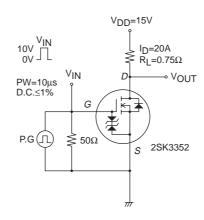


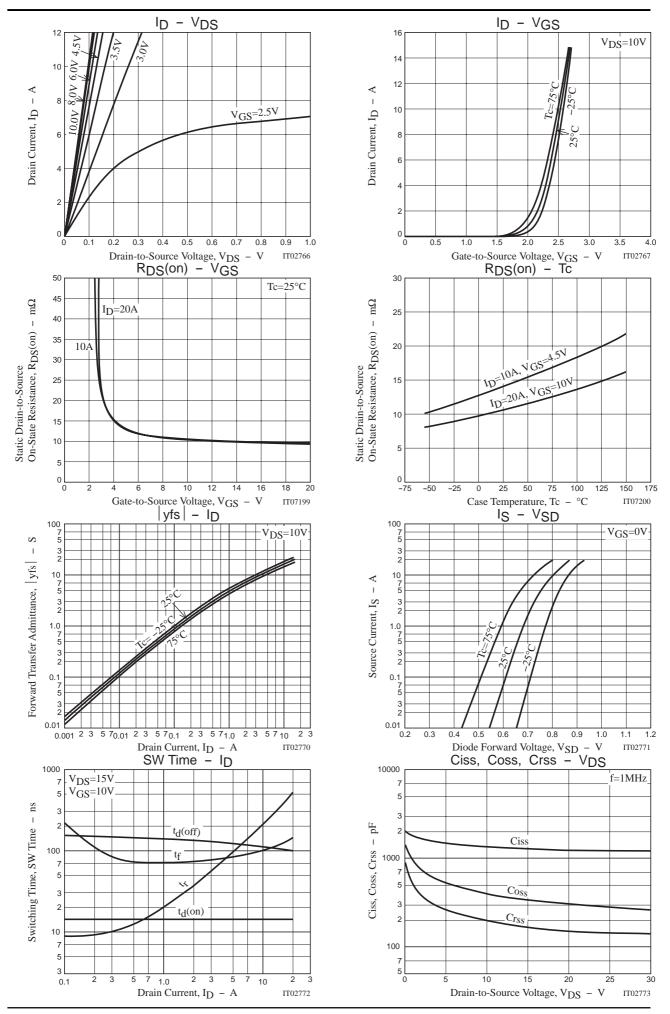
Package Dimensions

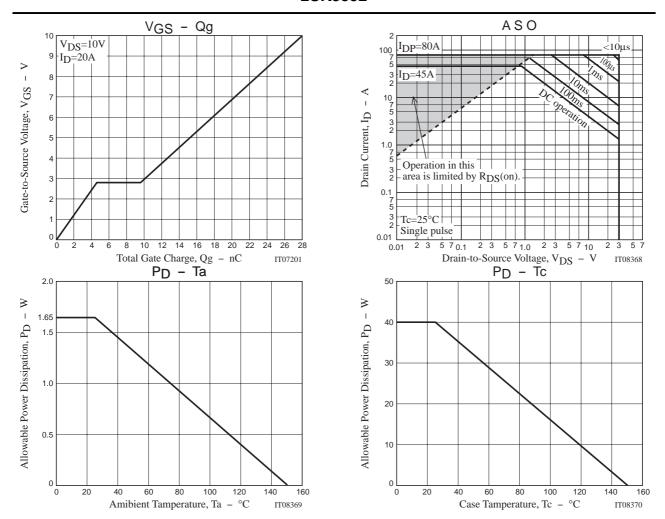
unit : mm 7042-001



Switching Time Test Circuit







Note on usage: Since the 2SK3352 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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